TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74VHC9125P,TC74VHC9125FT,TC74VHC9125FK, TC74VHC9126P,TC74VHC9126FT,TC74VHC9126FK

TC74VHC9125P/FT/FK 5-bit Universal Schmitt Buffer with 3-State Outputs TC74VHC9126P/FT/FK 5-bit Universal Schmitt Buffer with 3-State Outputs

The TC74VHC9125/9126 are an ultra-high-speed 5-bit Schmitt buffer fabricated using silicon-gate CMOS technology. The TC74VHC9125/9126 combines low power consumption of CMOS with Schottky TTL speeds.

Y1 to Y4 outputs can be put in the high-impedance state by placing a logic HIGH on the Enable ( $\overline{\mathbf{G}}$ ) input. The CONT input determines the logical inversion of data. A logic LOW on the CONT input configures the TC74VHC9125/9126 as an inverter; a logic HIGH on the CONT input configures the TC74VHC9125/9126 as a buffer.

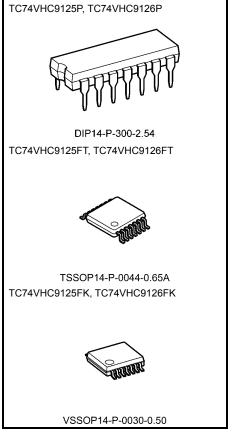
 $TC74VHC9125\ Y5$  output is an inverting type, and the  $TC74VHC9126\ Y5$  output is a non-inverting type.

All the inputs have hysteresis between the positive going and negative going thresholds. Thus the TC74VHC9125/9126 are capable of squaring up transitions of slowly changing input signals and provides an improved noise immunity.

Additionally, all the inputs have a newly developed protection circuit without a diode returned to  $V_{\rm CC}$ . This enables the inputs to be tolerant of up to 5 volts even when power supply is down. The input power-down protection capability makes the TC74VHC9125/9126 ideal for a wide range of applications, such as interfacing between different voltages, voltage translation from 5 V to 3 V and battery back-up circuits.

#### **Features**

- High speed:  $t_{pd} = 5.0 \text{ ns (typ.) (V}_{CC} = 5 \text{ V)}$
- Low supply current:  $I_{CC} = 2 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- All inputs are provided with power-down protection.
- Symmetrical rise and fall delays:  $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range:  $V_{CC}$  (opr) = 2 to 5.5 V

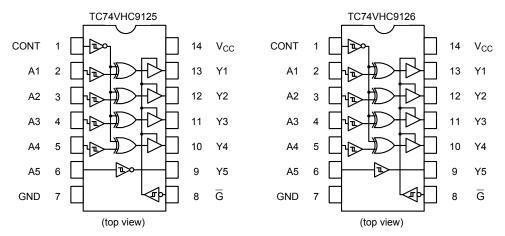


Weight

DIP14-P-300-2.54: 0.96 g ( typ.) TSSOP14-P-0044-0.65A: 0.06 g ( typ.) VSSOP14-P-0030-0.50: 0.02 g ( typ.)



## **Pin Assignment**



### **Truth Table**

	Inputs	Outputs			
G	CONT	A1~4	Y1~4		
Н	Х	Х	Z		
L	L L		Н		
L	L	Н	L		
L	Н	L	L		
L	Н	Н	Н		

Inputs	Outputs					
A5	Y5(9125)	Y5(9126)				
L	Н	L				
Н	L	Н				

X : Don't care

Z: High impedance



#### **Absolute Maximum Ratings (Note1)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V
DC input voltage	V <sub>IN</sub>	−0.5 to 7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	I <sub>OUT</sub>	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180(TSSOP/VSSOP)	mW
Storage temperature	T <sub>stg</sub>	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C shall be applied until 300 mW.

### **Operating Ranges (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	2.0 to 5.5	V
Input voltage	V <sub>IN</sub>	0 to 5.5	٧
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either  $V_{CC}$  or GND.



## **Electrical Characteristics**

### **DC Characteristics**

Characteristics	Symbol	Test Condition			Ta = 25°C		Ta = −40 to 85°C		Unit	
Griaracteristics Symbol				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Offic
		_		3.0	_	_	2.20	_	2.20	
Positive threshold voltage	$V_{P}$			4.5	_	_	3.15	_	3.15	
				5.5	1	1	3.85	_	3.85	V
				3.0	0.90	_	_	0.90	_	v
Negative threshold voltage	$V_N$		_	4.5	1.35	_	_	1.35	_	
, and the second				5.5	1.65	1	-	1.65		
					0.30	-	1.20	0.30	1.20	
Hysteresis voltage	$V_{H}$	_		4.5	0.40	_	1.40	0.40	1.40	٧
				5.5	0.50	_	1.60	0.50	1.60	
	Vон	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	2.0	1.9	2.0	_	1.9	_	
				3.0	2.9	3.0	_	2.9	_	
High-level output voltage				4.5	4.4	4.5	_	4.4	_	
			I <sub>OH</sub> = -4 mA	3.0	2.58	_	_	2.48	_	V
			I <sub>OH</sub> = -8 mA	4.5	3.94	_	_	3.80	_	
	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		2.0	_	0.0	0.1	_	0.1	v
			I <sub>OL</sub> = 50 μA	3.0	_	0.0	0.1	_	0.1	
Low-level output voltage				4.5	1	0.0	0.1	_	0.1	
			I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44	
			I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
3-state output off-state current	loz	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		5.5	_	_	±0.25	_	±2.50	μА
	l	V <sub>OUT</sub> = V <sub>CC</sub> or GND		0 to 5.5			±0.1		±1.0	
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = 5.5 V or GND		0 10 5.5	_	_	±0.1	_	±1.U	μА
Quiescent supply current	I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	2.0	_	20.0	μА



### AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics Symbo	Cumbal	Tes	st Condition		Ta = 25°C			Ta = −40 to 85°C		Unit		
	Symbol		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic		
			3.3 ± 0.3	15	_	6.0	8.0	1.0	10.0	- ns		
Propagation delay time	$t_{pLH}$			50	_	9.0	12.5	1.0	15.0			
(A1 to 4 - Y1 to 4)	$t_{pHL}$		5.0 ± 0.5	15	_	5.0	5.5	1.0	7.0			
			3.0 1 0.3	50	_	7.0	8.5	1.0	10.0			
			3.3 ± 0.3	15	_	8.5	11.5	1.0	13.5			
Propagation delay time	$t_{pLH}$		3.5 1 0.5	50	_	13.0	17.0	1.0	20.5	ns		
(CONT-Y1 to 4)	$t_{pHL}$		5.0 ± 0.5	15	_	6.5	8.0	1.0	9.5	ns		
			3.0 1 0.3	50	_	10.5	12.5	1.0	15.0			
		_	3.3 ± 0.3	15	_	6.0	8.0	1.0	10.0	- ns		
Propagation delay time	$t_{pLH}$			50	_	9.0	12.5	1.0	15.0			
(A5 – Y5)	$t_{pHL}$		5.0 ± 0.5	15	_	5.0	5.5	1.0	7.0			
				50	_	7.0	8.5	1.0	10.0			
	<sup>t</sup> pZL <sup>t</sup> pZH		3.3 ± 0.3	15	_	6.0	8.0	1.0	9.5	- ns		
3-state output enable		R <sub>L</sub> = 1 kΩ		50	_	10.5	13.5	1.0	16.5			
time			5.0 ± 0.5	15	_	4.5	5.5	1.0	6.5			
			3.0 1 0.5	50	_	9.0	10.5	1.0	12.5			
3-state output disable	$t_{pLZ}$	R <sub>L</sub> = 1 kΩ	$3.3 \pm 0.3$	50	_	12.5	13.5	1.0	16.0	ns		
time	t <sub>pHZ</sub>	KL = 1 K22	KL - 1 K22	IXL - 1 K22	$5.0 \pm 0.5$	50	_	9.0	9.5	1.0	11.0	115
Output to output skew	t <sub>osLH</sub>	(Note 1)	$3.3 \pm 0.3$	50	_	_	1.5	_	1.5	ns		
(A1 to 4 - Y1 to 4)	t <sub>osHL</sub>	(NOIE 1)	$5.0 \pm 0.5$	50	_	_	1.0	_	1.0	115		
Input capacitance	C <sub>IN</sub>	_		_	_	4	10	_	10	pF		
Output capacitance	C <sub>OUT</sub>	_		_	_	6	_	_	_	pF		
Power dissipation capacitance (Note 2)	C <sub>PD</sub>	f <sub>IN</sub> = 1 MHz	_	_	_	10	_	_	_	pF		

Note 1: Parameter guaranteed by design.

 $t_{\mathsf{OSLH}} = |t_{\mathsf{PLHm}} - t_{\mathsf{PLHn}}|, \, t_{\mathsf{OSHL}} = |t_{\mathsf{PHLm}} - t_{\mathsf{PHLn}}|$ 

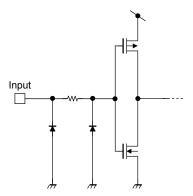
Note 2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 5 (per bit)$ 



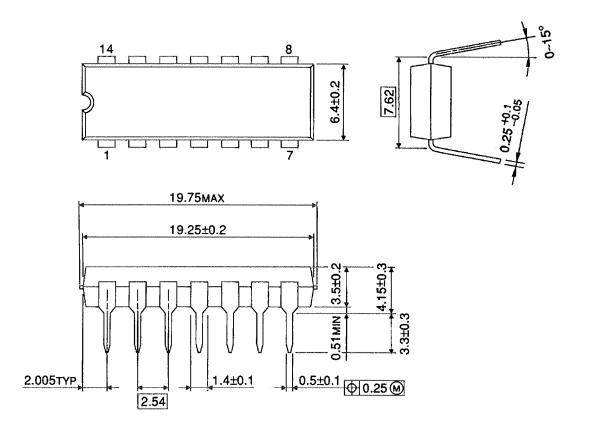
## **Input Equivalent Circuit**



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## **Package Dimensions**

DIP14-P-300-2.54 Unit: mm

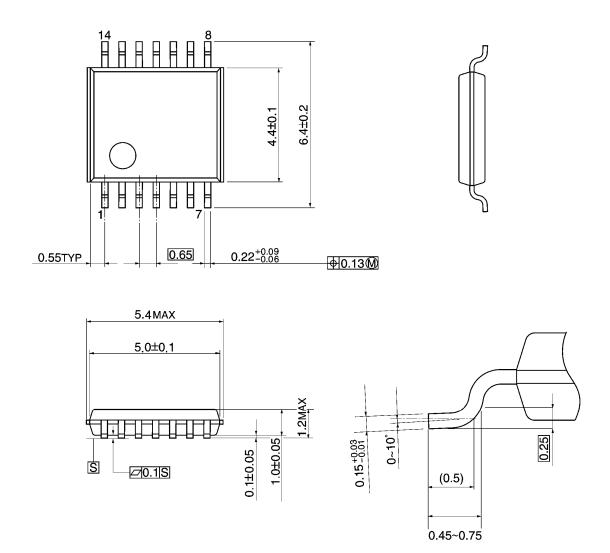


Weight: 0.96 g (typ.)

## **Package Dimensions**

TSSOP14-P-0044-0.65A

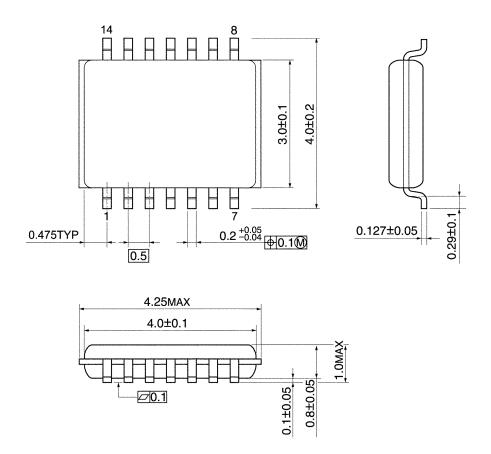
Unit: mm



Weight: 0.06 g (typ.)

## **Package Dimensions**

VSSOP14-P-0030-0.50 Unit: mm



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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